

Parameter	Value
V_{CEO}	50V
I_C	100mA
R_1	10k Ω

●Features

- 1) Built-In Biasing Resistor
- 2) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- 3) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 4) Only the on/off conditions need to be set for operation, making the circuit design easy.
- 5) Complementary PNP Types: DTA114T series
- 6) Complex transistors: UMH8N/ IMH8A/ EMG4/ UMG4N/ FMG4A (PNP type)
- 7) Lead Free/RoHS Compliant.

●Application

Switching circuit, Inverter circuit, Interface circuit, Driver circuit

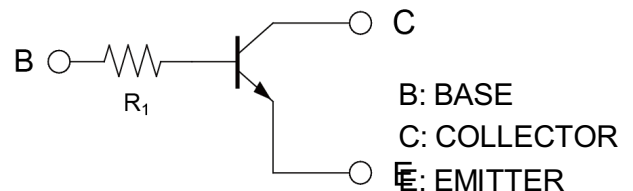
●Packaging specifications

Part No.	Package	Package size	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit.(pcs)	Marking
DTC114TM	VMT3	1212	T2L	180	8	8000	04
DTC114TEB	EMT3F	1616	TL	180	8	3000	04
DTC114TE	EMT3	1616	TL	180	8	3000	04
DTC114TUB	UMT3F	2021	TL	180	8	3000	04
DTC114TUA	UMT3	2021	T106	180	8	3000	04
DTC114TKA	SMT3	2928	T146	180	8	3000	04

●Outline

<p>VMT3</p> <p>DTC114TM (SC-105AA)</p>	<p>EMT3F</p> <p>DTC114TEB (SC-89)</p>
<p>EMT3</p> <p>DTC114TE SOT-416(SC-75A)</p>	<p>UMT3F</p> <p>DTC114TUB (SC-85)</p>
<p>UMT3</p> <p>DTC114TUA SOT-323(SC-70)</p>	<p>SMT3</p> <p>DTC114TKA SOT-346(SC-59)</p>

●Inner circuit



● Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter		Symbol	Values	Unit
Collector-base voltage		V_{CBO}	50	V
Collector-emitter voltage		V_{CEO}	50	V
Emitter-base voltage		V_{EBO}	5	V
Collector current		I_C	100	mA
Power dissipation	DTC114TM	P_D^{*1}	150	mW
	DTC114TEB		150	
	DTC114TE		150	
	DTC114TUB		200	
	DTC114TUA		200	
	DTC114TKA		200	
Junction temperature		T_j	150	$^\circ\text{C}$
Range of storage temperature		T_{stg}	-55 to +150	$^\circ\text{C}$

● Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Collector-base breakdown voltage	BV_{CBO}	$I_C = 50\mu\text{A}$	50	-	-	V
Collector-emitter breakdown voltage	BV_{CEO}	$I_C = 1\text{mA}$	50	-	-	V
Emitter-base breakdown voltage	BV_{EBO}	$I_E = 50\mu\text{A}$	5	-	-	V
Collector cut-off current	I_{CBO}	$V_{CB} = 50\text{V}$	-	-	0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 4\text{V}$	-	-	0.5	μA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C / I_B = 10\text{mA} / 1\text{mA}$	-	-	0.3	V
DC current gain	h_{FE}	$V_{CE} = 5\text{V}, I_C = 1\text{mA}$	100	250	600	-
Input resistance	R_1	-	7	10	13	k Ω
Transition frequency	f_T^{*2}	$V_{CE} = 10\text{V}, I_E = -5\text{mA},$ $f = 100\text{MHz}$	-	250	-	MHz

*1 Each terminal mounted on a reference footprint

*2 Characteristics of built-in transistor

●Electrical characteristic curves(Ta=25°C)

Fig.1 Grounded emitter propagation characteristics

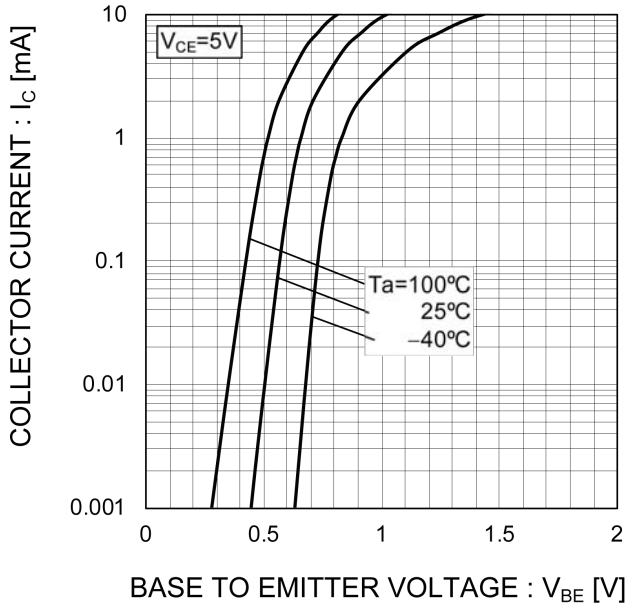


Fig.2 Grounded emitter output characteristics

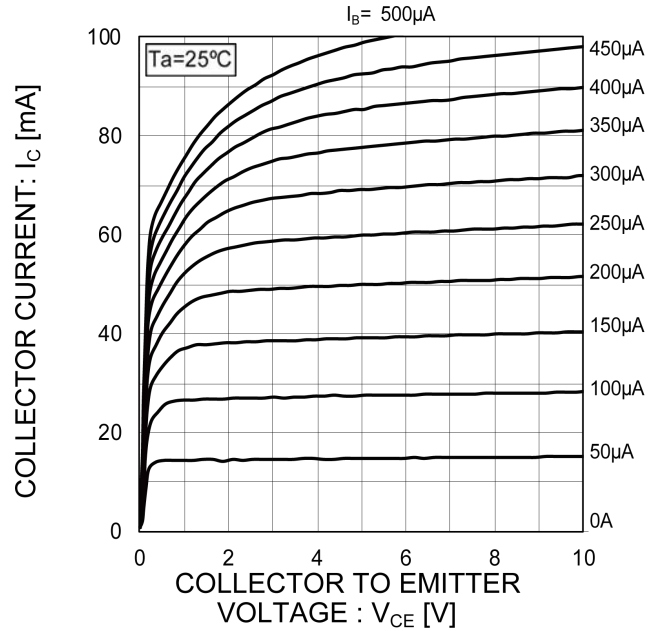


Fig.3 DC Current gain vs. Collector Current

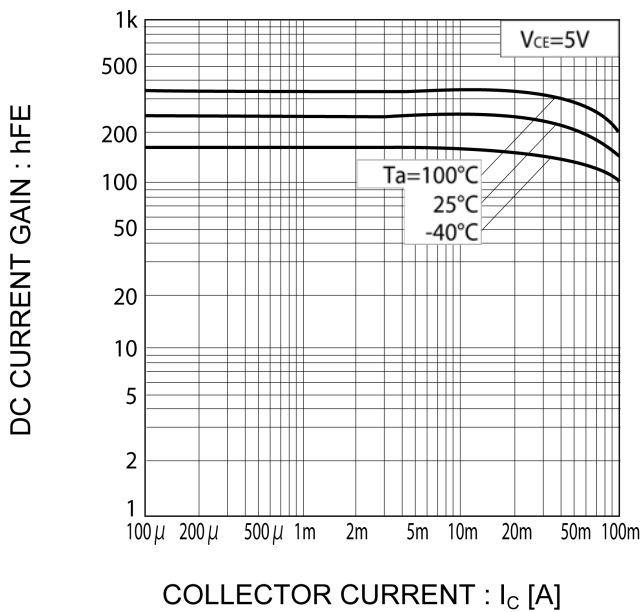
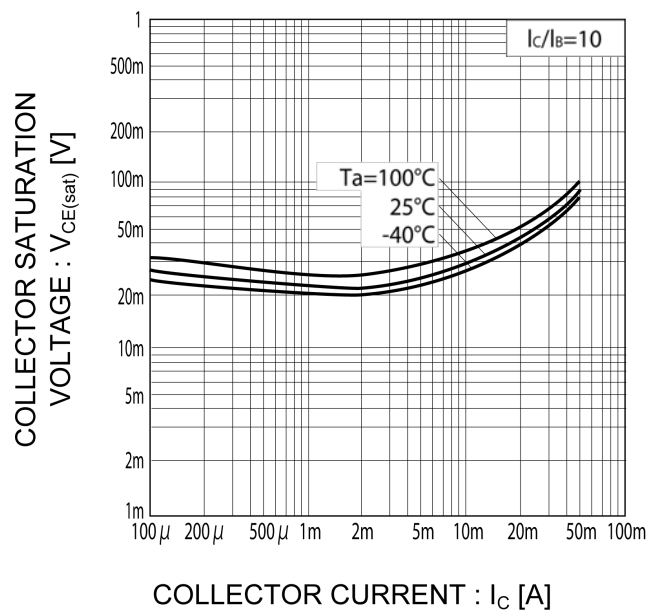
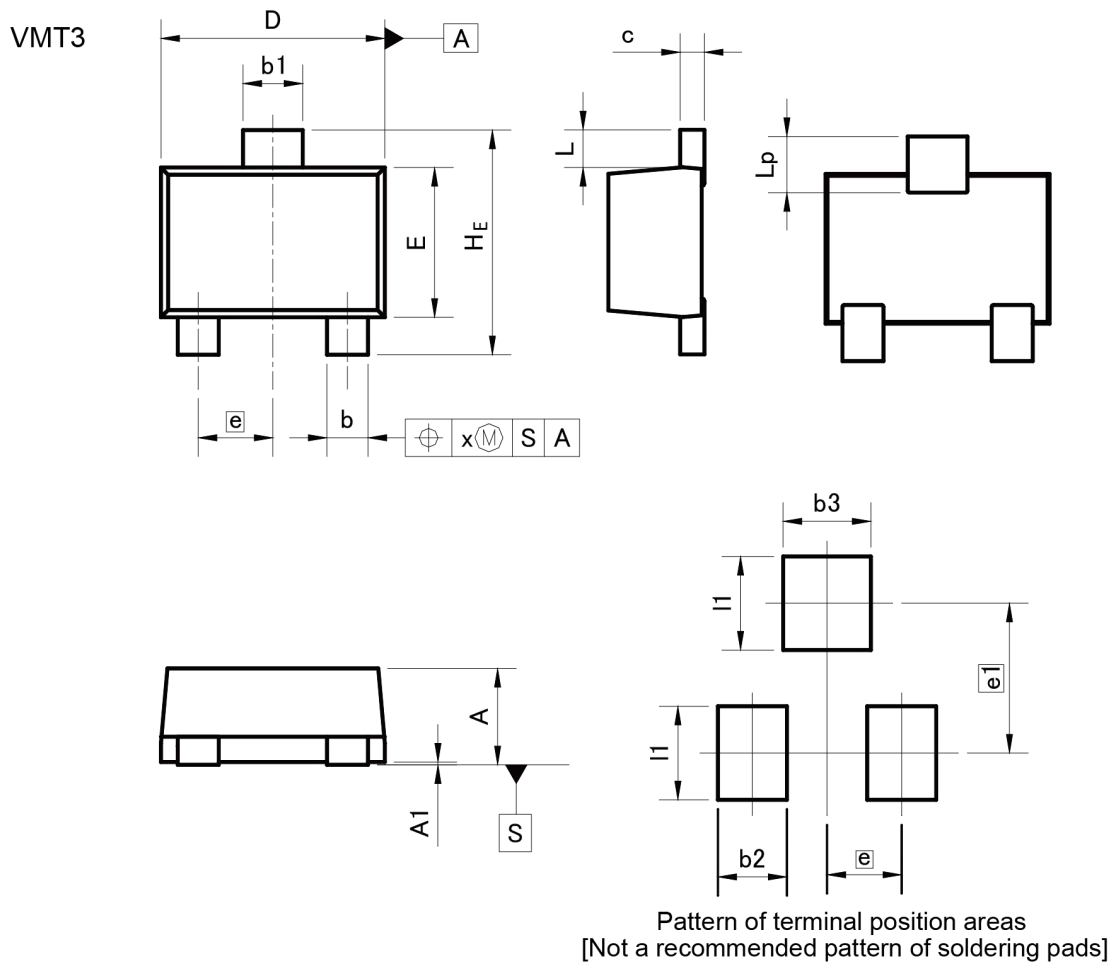


Fig.4 Collector-emitter saturation voltage vs. Collector Current



●Dimensions



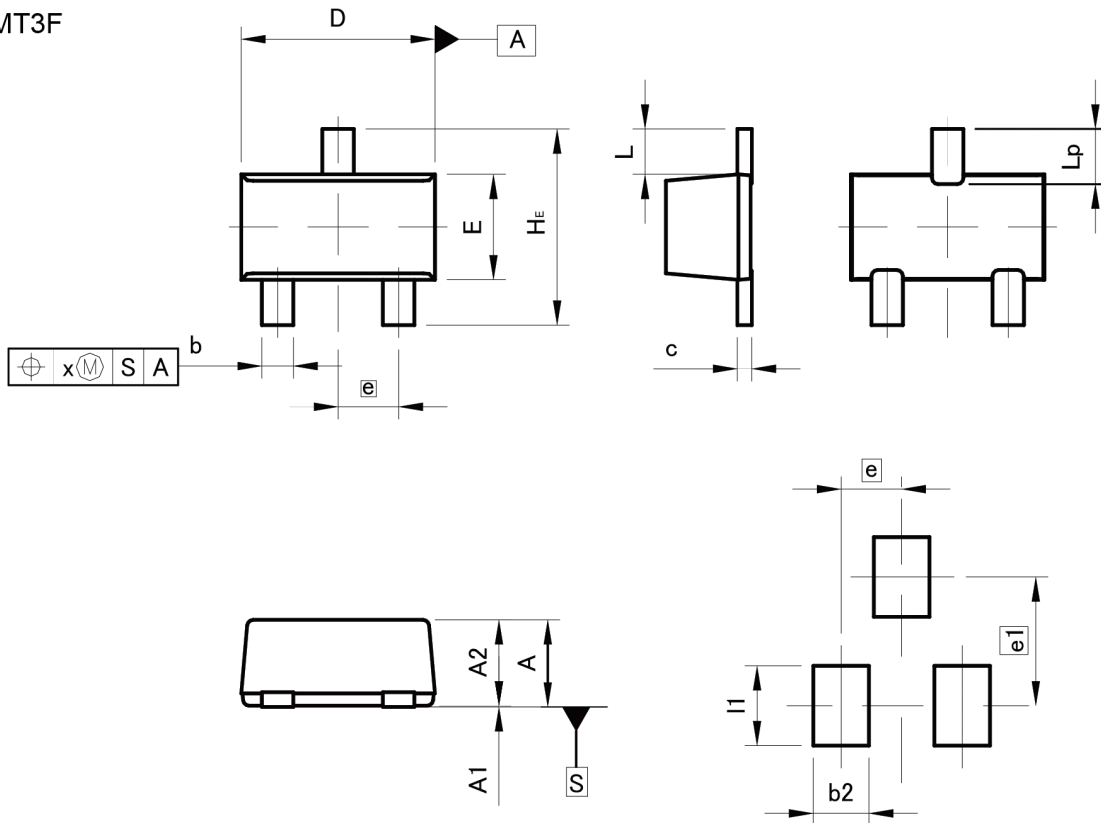
DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.45	0.55	0.018	0.022
A1	0.00	0.10	0.000	0.004
b	0.17	0.27	0.007	0.011
b1	0.27	0.37	0.011	0.015
c	0.08	0.18	0.003	0.007
D	1.10	1.30	0.043	0.051
E	0.70	0.90	0.028	0.035
e	0.40		0.02	
HE	1.10	1.30	0.043	0.051
L	0.10	0.30	0.004	0.012
Lp	0.20	0.40	0.008	0.016
x	-	0.10	-	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	-	0.37	-	0.015
b3	-	0.47	-	0.019
e1	0.80		0.031	
I1	-	0.50	-	0.020

Dimension in mm/inches

●Dimensions

EMT3F



Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

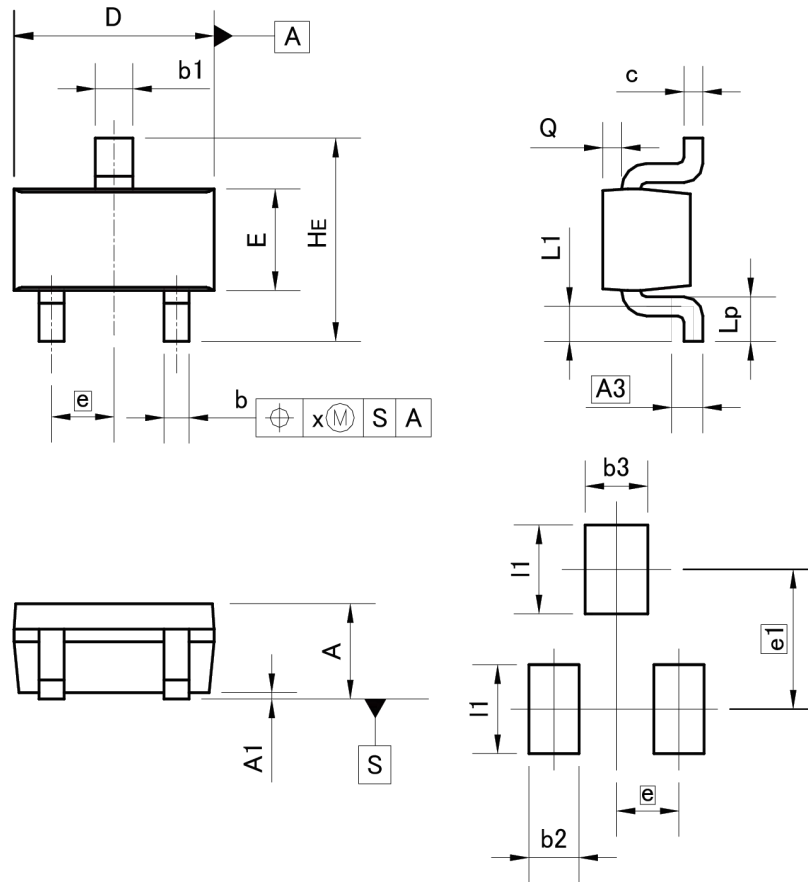
DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.65	0.85	0.026	0.033
A1	0.00	0.10	0.000	0.004
A2	0.60	0.80	0.024	0.031
b	0.21	0.36	0.008	0.014
c	0.08	0.18	0.003	0.007
D	1.50	1.70	0.059	0.067
E	0.76	0.96	0.030	0.038
e	0.50		0.020	
HE	1.50	1.70	0.059	0.067
L	0.37		0.015	
Lp	0.35	0.55	0.014	0.022
x	-	0.10	-	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	-	0.46	-	0.018
e1	-	1.05	-	0.041
l1	-	0.65	-	0.026

Dimension in mm/inches

●Dimensions

EMT3



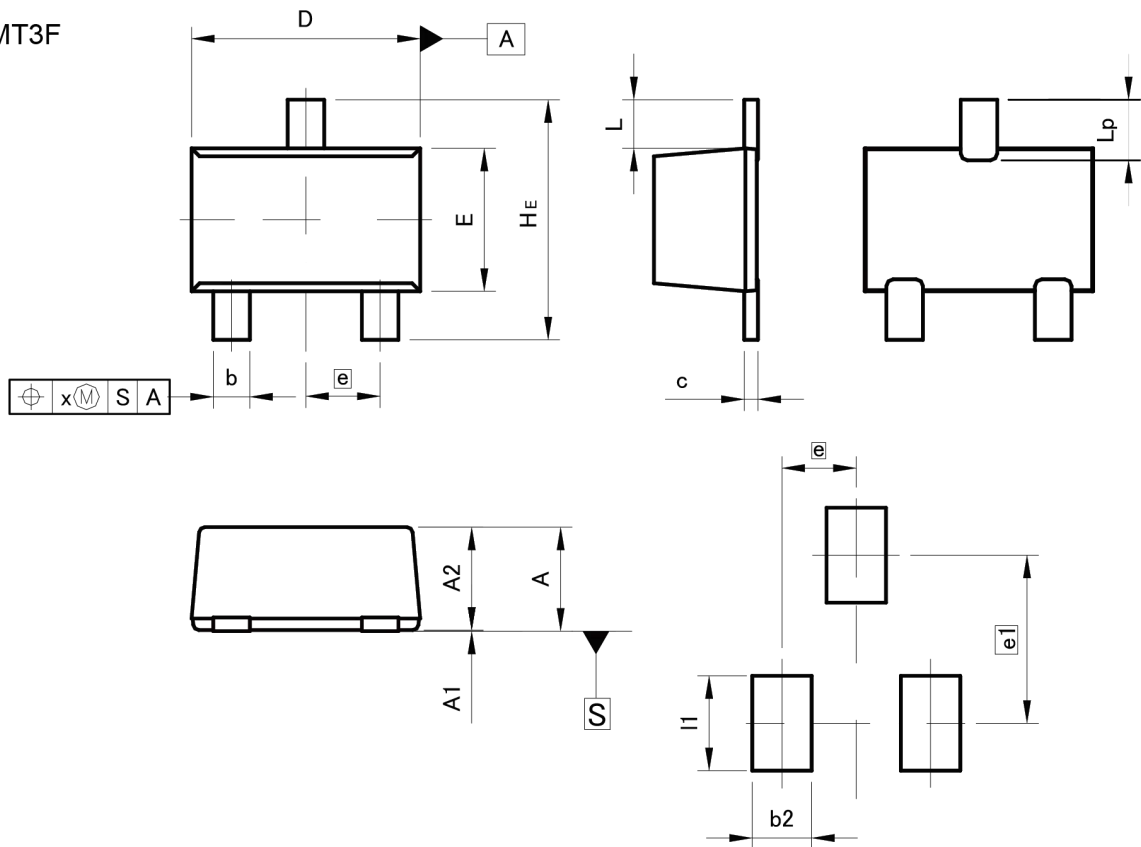
Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.60	0.80	0.024	0.031
A1	0.00	0.10	0.000	0.004
A3	0.25		0.010	
b	0.15	0.30	0.006	0.012
b1	0.25	0.40	0.010	0.016
c	0.10	0.20	0.004	0.008
D	1.50	1.70	0.059	0.067
E	0.70	0.90	0.028	0.035
e	0.50		0.020	
HE	1.40	1.80	0.055	0.071
L1	0.10	-	0.004	-
Lp	0.15	-	0.006	-
Q	0.05	0.25	0.002	0.010
x	-	0.10	-	0.004
DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	-	0.40	-	0.016
b3	-	0.50	-	0.020
e1	1.10		0.043	
I1	-	0.70	-	0.028

Dimension in mm/inches

●Dimensions

UMT3F



Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

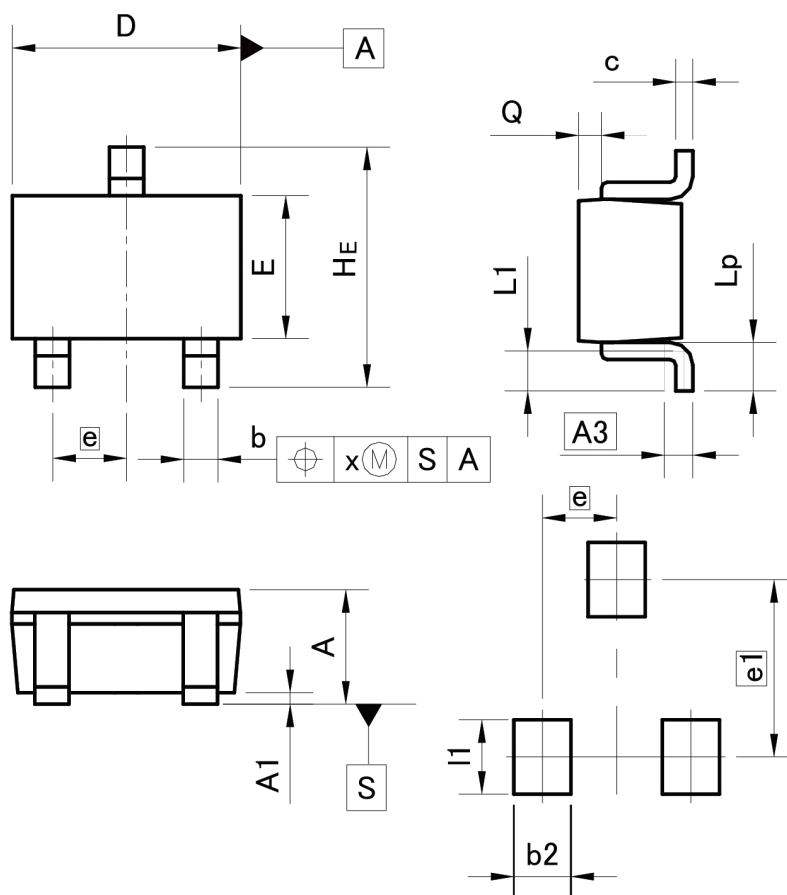
DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.85	1.05	0.033	0.041
A1	0.00	0.10	0.000	0.004
A2	0.80	1.00	0.031	0.039
b	0.27	0.42	0.011	0.017
c	0.08	0.18	0.003	0.007
D	1.90	2.10	0.075	0.083
E	1.15	1.35	0.045	0.053
e	0.65		0.026	
HE	2.00	2.20	0.079	0.087
L	0.43		0.017	
Lp	0.43	0.63	0.017	0.025
x	-	0.10	-	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	-	0.52	-	0.020
e1	1.47		0.058	
l1	-	0.83	-	0.033

Dimension in mm/inches

●Dimensions

UMT3



Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

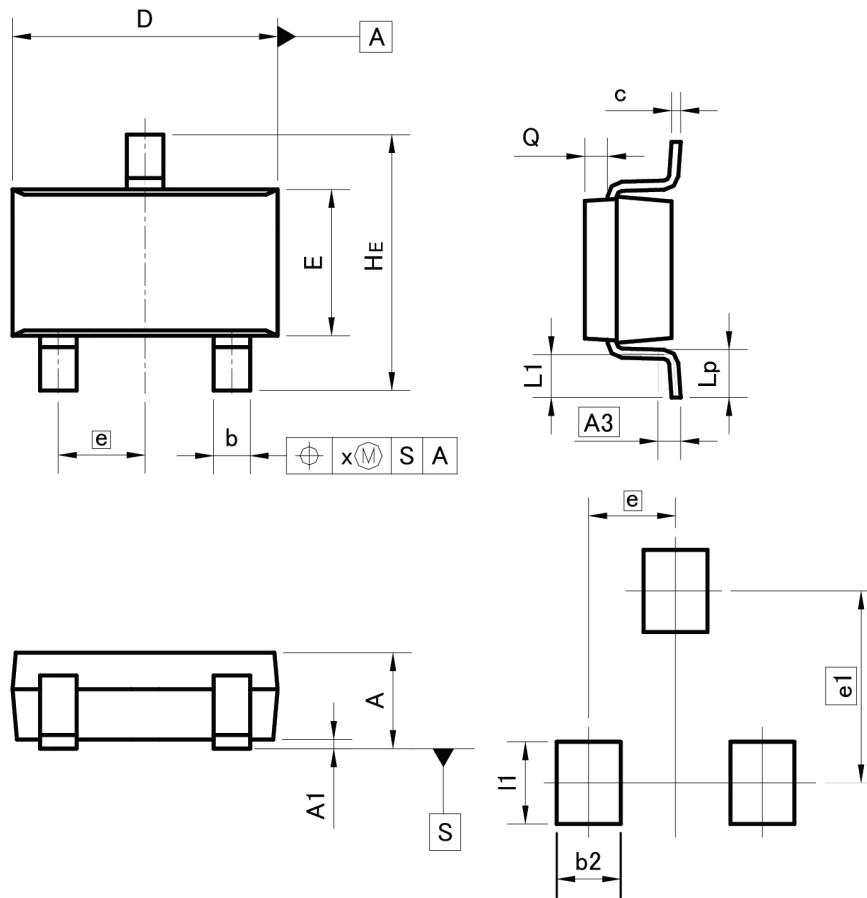
DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.80	1.00	0.031	0.039
A1	0.00	0.10	0.000	0.004
A3	0.25		0.010	
b	0.15	0.30	0.006	0.012
c	0.10	0.20	0.004	0.008
D	1.90	2.10	0.075	0.083
E	1.15	1.35	0.045	0.053
e	0.65		0.026	
HE	2.00	2.20	0.079	0.087
L1	0.20	0.50	0.008	0.020
Lp	0.25	0.55	0.010	0.022
Q	0.10	0.30	0.004	0.012
x	-	0.10	-	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	-	0.50	-	0.020
e1	1.55		0.061	
l1	-	0.65	-	0.026

Dimension in mm/inches

●Dimensions

SMT3



Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.00	1.30	0.039	0.051
A1	0.00	0.10	0.000	0.004
A3	0.25		0.010	
b	0.35	0.50	0.014	0.020
c	0.09	0.25	0.004	0.010
D	2.80	3.00	0.110	0.118
E	1.50	1.80	0.059	0.071
e	0.95		0.037	
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.20	0.30	0.008	0.012
x	-	0.10	-	0.004
y	-	0.10	-	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	-	0.60	-	0.024
e1	2.10		0.083	
l1	-	0.90	-	0.035

Dimension in mm/inches

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